



深圳市诚芯微科技股份有限公司

SHENZHEN CHENGXINWEI TECHNOLOGY CO., LTD.

N+N-channel Enhancement Mode Mosfet

CX3622DE

DESCRIPTION

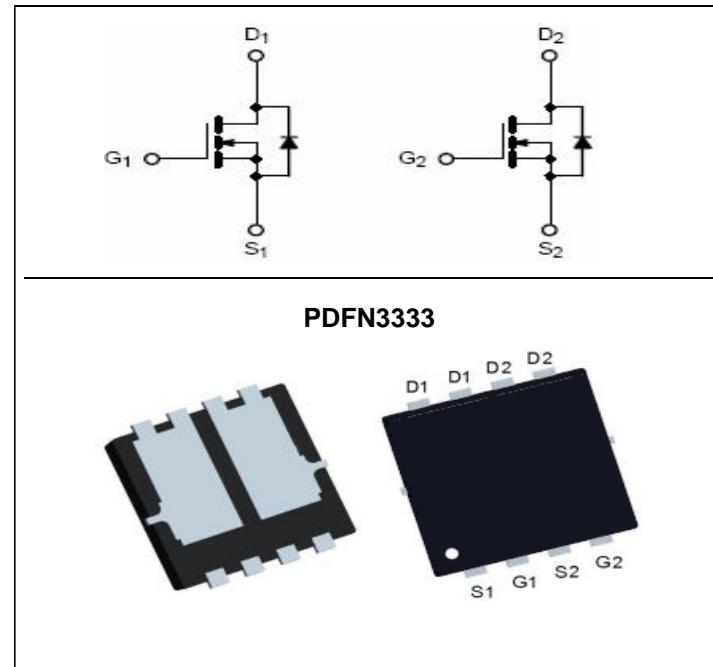
The CX3622DE uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- RDS(ON) <10 mΩ @ VGS=10V
RDS(ON) <13 mΩ @ VGS=4.5V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C=25^\circ\text{C}$	I_D	35	A
	$T_C=100^\circ\text{C}$		22	
Pulsed Drain Current ^A		I_{DM}	140	A
Total Power Dissipation	$T_C=25^\circ\text{C}$	P_D	20	W
	$T_C=100^\circ\text{C}$		15	W
Single Pulse Avalanche Energy ^B		E_{AS}	16	mJ
Thermal Resistance Junction-to-Case ^C		$R_{\theta JC}$	45	°C/W
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+155	°C